

2013年 発表文献リスト

(論文発表)

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2. Md. T. Hasan, T. Asano, H. Tokuda, and M. Kuzuhara, "Current collapse suppression by gate field plate in AlGa<sub>N</sub>/Ga<sub>N</sub> HEMTs," *IEEE Electron Device Lett.* vol. 34, 1379 Nov. (2013).
3. T. Kojima, H. Tokuda, and M. Kuzuhara, "Comparison of 2DEG density and mobility increase by annealing AlGa<sub>N</sub>/ Ga<sub>N</sub> heterostructures deposited with Ti/Al, Ti/Au, V/Au, and Ni/Au," *Phys. Status Solidi C* vol. 10, 1405 Nov. (2013).

(国際会議発表)

1. T. Kojima, H. Tokuda, and M. Kuzuhara, "Remarkable increase in 2DEG density by annealing AlGa<sub>N</sub>/Ga<sub>N</sub> heterostructures deposited with Ti/Al," 40<sup>th</sup> Intl. Symposium on Compound Semiconductors, May, 2013.
2. Md. T. Hasan, T. Asano, H. Tokuda, and M. Kuzuhara, "Effect of field plate on dynamic ON-resistance in AlGa<sub>N</sub>/Ga<sub>N</sub> HEMTs," 40<sup>th</sup> Intl. Symposium on Compound Semiconductors, May, 2013.
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4. K. Tone, H. Tokuda, and M. Kuzuhara, "V/Al-based ohmic contact formation to n-GaN using low temperature annealing," Intl. Meeting for Future of Electron Devices, Kansai, June, 2013.
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6. Y. Sakaida, H. Tokuda, and M. Kuzuhara, "Electrical characterization of AlGa<sub>N</sub>/ Ga<sub>N</sub> HEMTs fabricated on CF<sub>4</sub> plasma-treated AlGa<sub>N</sub> surface," Intl. Meeting for Future of Electron Devices, Kansai, June, 2013.
7. Y. Kobayashi, T. Saito, H. Tokuda, and M. Kuzuhara, "Electrical characterization of lateral tunnel junctions fabricated on AlGa<sub>N</sub>/ Ga<sub>N</sub> heterostructures," Intl. Meeting for Future of Electron Devices, Kansai, June, 2013.
8. K. Akira, T. Asano, H. Tokuda, and M. Kuzuhara, "High-voltage AlGa<sub>N</sub>/Ga<sub>N</sub> HEMTs fabricated on free-standing Ga<sub>N</sub> substrates," Intl. Meeting for Future of Electron Devices, Kansai, June, 2013.
9. K. Kodama, T. Tokuda, and M. Kuzuhara, "Improved dependence of gate-to-drain distance on electron velocity in AlGa<sub>N</sub>/ Ga<sub>N</sub> HEMTs," Intl. Workshop on Computational Electronics, June, 2013.
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high-temperature characteristics of AlGa<sub>N</sub>/Ga<sub>N</sub> MIS HEMTs with ZrO<sub>2</sub>/Al<sub>2</sub>O<sub>3</sub> dual dielectric films,” Intl. Conf. on Solid State Devices and Materials, Fukuoka, Japan, Sept., pp.922-923, 2013.

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12. K. Akira, H. Tokuda, and M. Kuzuhara, “Current collapse measurements for AlGa<sub>N</sub>/Ga<sub>N</sub> HEMTs fabricated on free-standing Ga<sub>N</sub> substrates,” 10<sup>th</sup> Topical Workshop on Heterostructure Microelectronics, Sept., 2013.
13. M. Kuzuhara and H. Tokuda, “Recent progress in Ga<sub>N</sub>-based electronic devices,” TNS 2013, Tsukuba, Dig., p.15, July (2013). (Invited).